



# FUKUCOM COMPANY LTD.

## 福靈有限公司

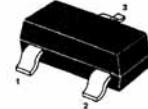
FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314      FAX: 852-2790 0206

### S8050LT1

**NPN Epitaxial Silicon Transistor**

- Complement to S8550LT1
- Collector Current:  $I_c=500\text{mA}$
- High Total Power Dissipation:  $P_c=225\text{mW}$



1. Base 2. Emitter 3. Collector  
SOT-23 Plastic Package

**Absolute Maximum Ratings**  $T_a=25^\circ\text{C}$  unless otherwise noted

Symbol	Characteristic	Value	Units
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	25	V
$V_{EB}$	Emitter-Base Voltage	6	V
$I_c$	Collector Current	500	mA
$P_D$	Collector Dissipation $T_a=25^\circ\text{C}^*$	225	mW
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55~150	$^\circ\text{C}$

**Electrical Characteristics**  $T_a=25^\circ\text{C}$  unless otherwise noted

Symbol	Characteristic	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C=100\ \mu\text{A}, I_E=0$	40			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}, I_B=0$	25			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E=100\ \mu\text{A}, I_C=0$	6			V
$I_{CBO}$	Collector-Base Cutoff Current	$V_{CB}=35\text{V}, I_E=0\text{V}$			100	$\eta\text{ A}$
$I_{EBO}$	Emitter-Base Cutoff Current	$V_{EB}=6\text{V}, I_C=0$			100	$\eta\text{ A}$
$h_{FE}$	DC Current Gain Group C Group D	$V_{CE}=1\text{V}, I_C=50\text{mA}$			120 180	200 300
$h_{FE}$	DC Current Gain	$V_{CE}=1\text{V}, I_C=5\text{mA}$ $V_{CE}=1\text{V}, I_C=500\text{mA}$	45 30			
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C=500\text{mA}, I_B=50\text{mA}$			0.6	V
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C=500\text{mA}, I_B=50\text{mA}$			1.2	V
$V_{BE(\text{ON})}$	Base-Emitter On Voltage	$V_{CE}=1\text{V}; I_C=10\text{mA}$			1.0	V
$C_{OB}$	Output Capacitance	$V_{CB}=10\text{V}; I_E=0\text{ f=MHz}$		9		pf
$f_T$	Current Gain-Bandwidth Product	$V_{CE}=10\text{V}, I_C=50\text{mA}$	100	190		MHz
Marking : A6(Group)						

\* Total Device Dissipation :  $FR=1\times 0.75 \times 0.062$  in Board, Derate  $25^\circ\text{C}$

# Pulse Test : Pulse Width  $\leq 300\text{uS}$ , Duty cycle  $\leq 2\%$



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